

N-channel TrenchMOS SiliconMAX standard level FET 3 October 2013 Product data sheet

### 1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 2. Features and benefits

- Higher operating power due to low thermal resistance
- Suitable for high frequency applications due to fast switching characteristics

### 3. Applications

- Class D amplifier
- DC-to-DC converters
- Motion control
- Switched-mode power supplies

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C		-	-	150	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>		-	-	43	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	113	W
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10		-	46	59	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; V <sub>DS</sub> = 75 V; Fig. 11; Fig. 12		-	9.1	-	nC



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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UTA
4	G	gate	មុច្ចមុ	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN059-150Y	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN059-150Y	059150

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

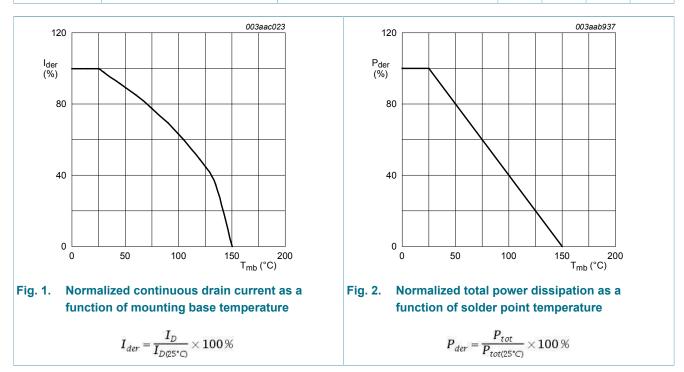
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	150	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \Omega$	-	150	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u> ; <u>Fig. 3</u>	-	43	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	-	27.7	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3	-	129	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	113	W
T <sub>stg</sub>	storage temperature		-55	150	°C

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## **PSMN059-150Y**

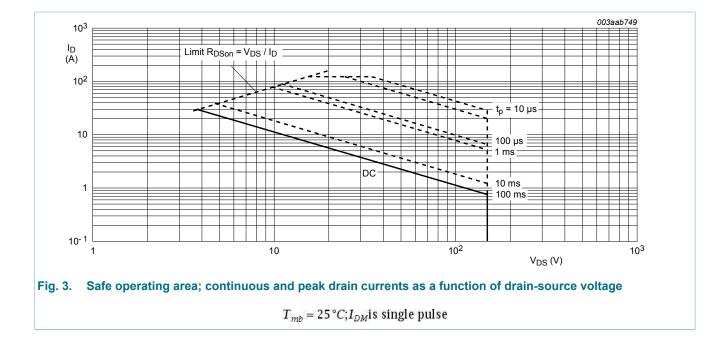
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Symbol	Parameter	Conditions	Min	Мах	Unit		
Tj	junction temperature		-55	150	°C		
Source-dra	in diode	· · · · · · ·	- I				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	52	А		
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$	-	208	А		
Avalanche	Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} V_{GS} &= 10 \text{ V};  \text{T}_{j(init)} = 25 ^\circ\text{C};  \text{I}_D = 12.1 \text{ A}; \\ V_{sup} &\leq 150 \text{ V}; \text{ unclamped};  \text{t}_p = 0.21 \text{ ms}; \\ \text{R}_{GS} &= 50  \Omega \end{split}$	-	255	mJ		



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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	mounted on a printed-circuit board; vertical in still air; <u>Fig. 4</u>	-	-	1.1	K/W

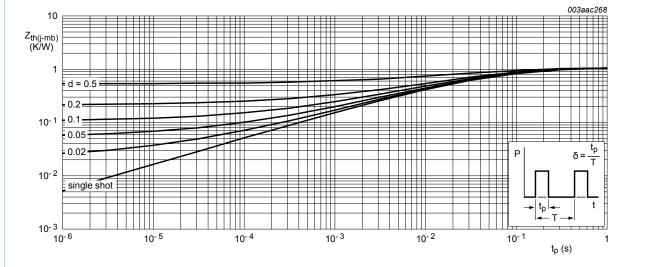


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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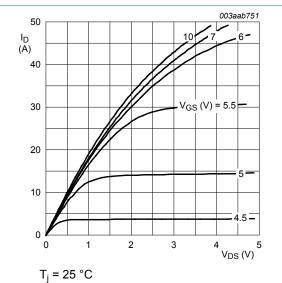
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				_
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	150	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	133	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 7; Fig. 8	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; Fig. 7; Fig. 8	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 7; Fig. 8	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 120 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 120 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	-	46	59	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 150 °C; Fig. 9; Fig. 10	-	101	135	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	naracteristics	· · ·	I		1	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 12 A; V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 10 V;	-	27.9	-	nC
Q <sub>GS</sub>	gate-source charge	<u>Fig. 11; Fig. 12</u>	-	6.3	-	nC
Q <sub>GD</sub>	gate-drain charge		-	9.1	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 12 A; V <sub>DS</sub> = 75 V; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1529	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	208	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	66	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 75 V; R <sub>L</sub> = 3 Ω; V <sub>GS</sub> = 10 V;	-	14.2	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 5.6 Ω	-	42	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 [	-	54.2	-	ns
t <sub>f</sub>	fall time	1	-	11.1	-	ns
Source-drai	in diode	· ·		1		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 12 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 14</u>	-	0.9	1.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 12 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V	-	67	-	ns
Q <sub>r</sub>	recovered charge	$I_{\rm S}$ = 12 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V	-	226	-	nC





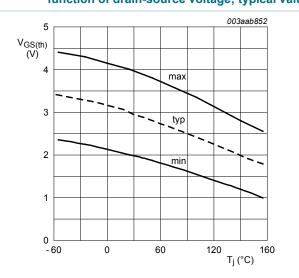
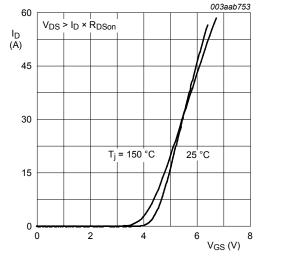


Fig. 7. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 m A; V_{DS} = V_{GS}$$



 $T_i$  = 25 °C and 150 °C;  $V_{DS}$  >  $I_D \times R_{DSon}$ 



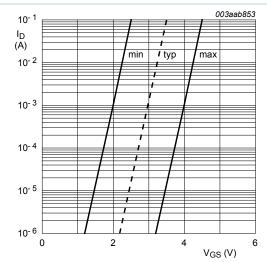


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

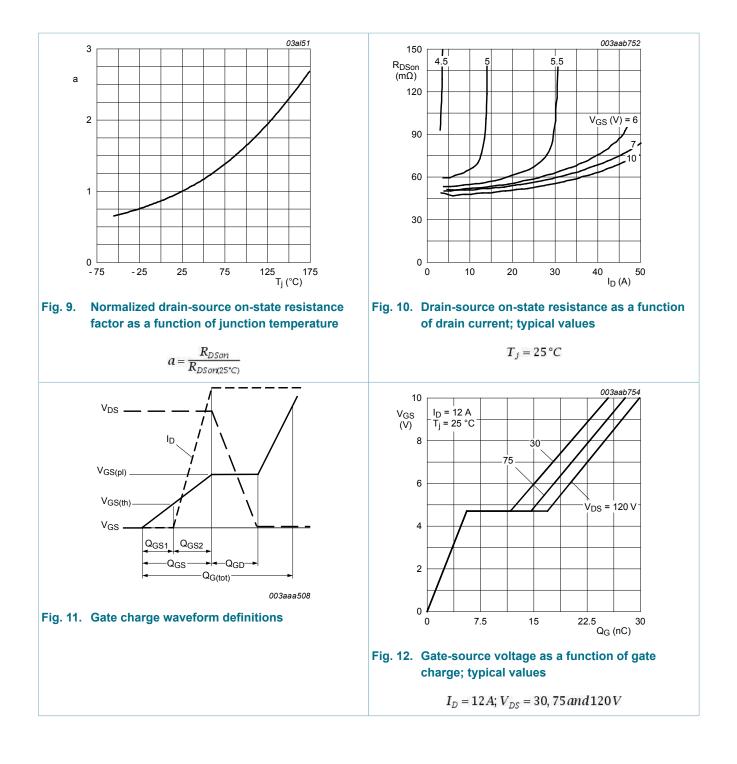
 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 

**Product data sheet** 

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## **PSMN059-150Y**

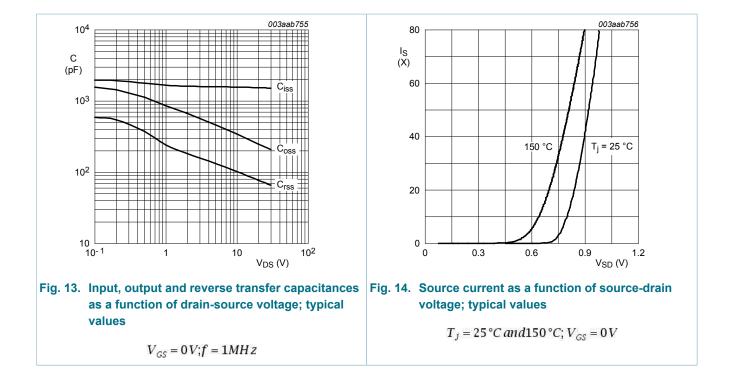
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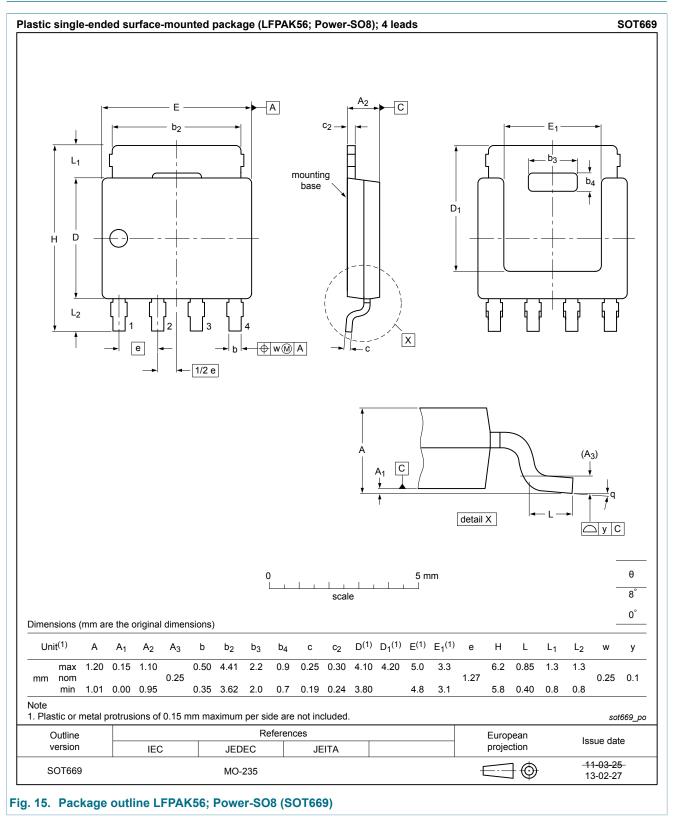
## **PSMN059-150Y**

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### **11. Package outline**



PSMN059-150Y

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